



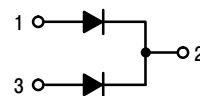
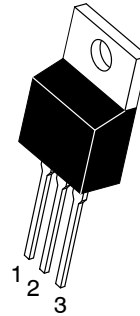
MBR1040CTG THRU MBR10200CTG

10.0 AMPS. Schottky Barrier Rectifiers

Features

- Metal silicon junction, majority carrier conduction
- Plastic material used carries Underwriters Laboratory Classifications 94V-0
- High surge capability
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- Guardring for overvoltage protection
- High temperature soldering guaranteed: 260°C/10 seconds, 0.25" (6.35mm) from case
- Green compound with suffix "G" on packing code & prefix "G" on datecode.

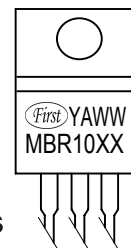
TO- 220AB



Mechanical Data

- Cases: JEDEC TO-220AB molded plastic
- Polarity: As marked
- Terminals: Pure tin plated, lead free. solderable per MIL-STD-750, Method 2026
- Mounting position: Any
- Weight: 1.88grams
- Mounting torque: 5 in. - lbs. max

Marking Diagram



Y = Year
A = Assembly Location
WW = Work Week
MBR10XX = Specific Device Code

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	MBR 1040 CTG	MBR 1045 CTG	MBR 1050 CTG	MBR 1060 CTG	MBR 1080 CTG	MBR 10100 CTG	MBR 10150 CTG	MBR 10200 CTG	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	45	50	60	80	100	150	200	V
Maximum RMS Voltage	V _{RMS}	28	31	35	42	56	70	105	140	V
Maximum DC Blocking Voltage	V _{DC}	40	45	50	60	80	100	150	200	V
Maximum Average Forward Rectified Current at Tc=125°C	I _{F(AV)}	10								A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20KHz) at Tc=125°C	I _{FRM}	10								A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	120								A
Peak Repetitive Reverse Surge Current (Note 2)	I _{RRM}	1.0		0.5						A
Maximum Instantaneous Forward Voltage at: I _F =5A, T _A =25°C I _F =5A, T _A =125°C I _F =10A, T _A =25°C I _F =10A, T _A =125°C	V _F	0.70 0.55 0.80 0.70	0.74 0.60 0.85 0.74		0.80 0.70 0.90 0.80		0.85 0.75 0.95 0.85		V	
Maximum Instantaneous Reverse Current @ T _A =25 °C at Rated DC Blocking Voltage (Note 1) @ T _A =125 °C	I _R	0.1								mA
		15		10		2.0		5.0		mA
Voltage Rate of Change (Rated V _R)	dV/dt	10,000								V/uS
Maximum Typical Thermal Resistance (Note 3)	RθJC	1.5								°C/W
Operating Junction Temperature Range	T _J	-65 to +150								°C
Storage Temperature Range	T _{STG}	-65 to +175								°C

Notes: 1. Pulse Test: 300 μs Pulse Width, 1% Duty Cycle

2. 2.0 μs Pulse Width, $f=1.0$ KHz

3. Mount on Heatsink Size of 2 in x 3 in x 0.25in Al-Plate.

RATINGS AND CHARACTERISTIC CURVES

FIG.1- FORWARD CURRENT DERATING CURVE

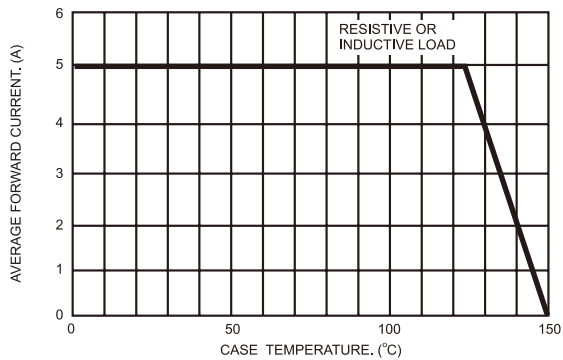


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

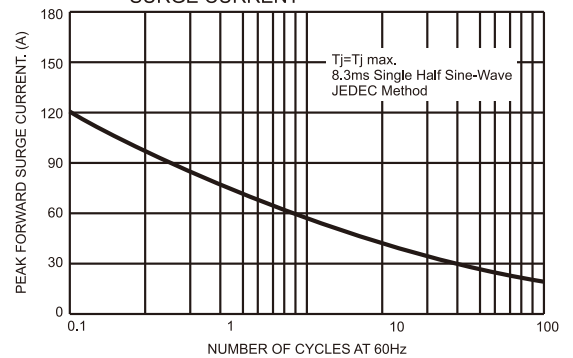


FIG.3- TYPICAL FORWARD CHARACTERISTICS

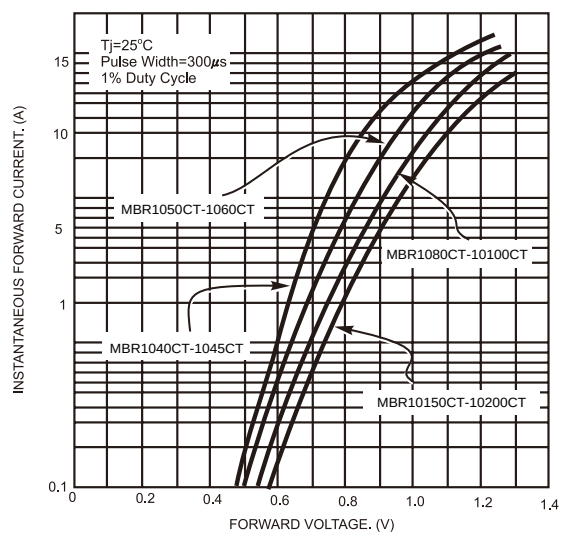
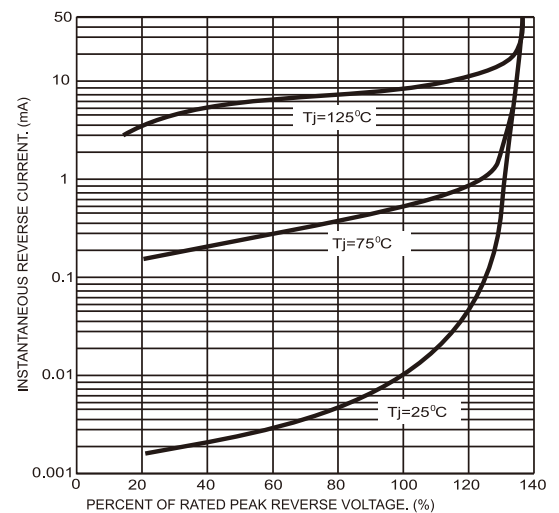


FIG.4- TYPICAL REVERSE CHARACTERISTICS



G C S

FIG.5- TYPICAL JUNCTION CAPACITANCE

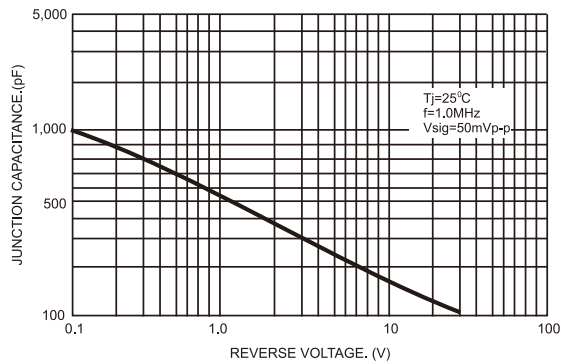
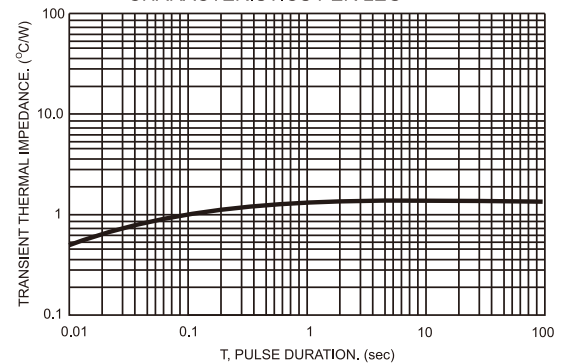
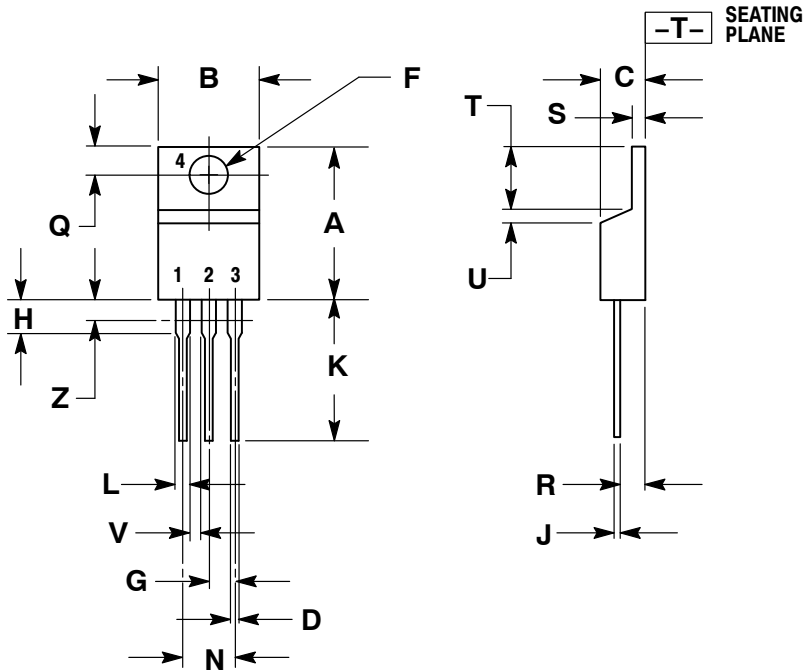


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS PER LEG



TO-220AB



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:

- PIN 1. ANODE
 2. CATHODE
 3. ANODE
 4. CATHODE